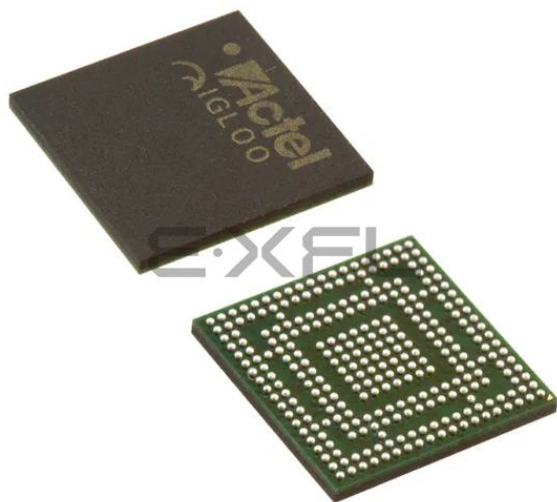




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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	13824
Total RAM Bits	110592
Number of I/O	215
Number of Gates	600000
Voltage - Supply	1.14V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 85°C (TA)
Package / Case	281-TFBGA, CSBGA
Supplier Device Package	281-CSP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/agl600v2-csg281i

Temperature Grade Offerings

Package	AGL015 ¹	AGL030	AGL060	AGL125	AGL250	AGL400	AGL600	AGL1000
					M1AGL250		M1AGL600	M1AGL1000
QN48	–	C, I	–	–	–	–	–	–
QN68	C, I	–	–	–	–	–	–	–
UC81	–	C, I	–	–	–	–	–	–
CS81	–	C, I	–	–	–	–	–	–
CS121	–	–	C, I	C, I	–	–	–	–
VQ100	–	C, I	C, I	C, I	C, I	–	–	–
QN132 ²	–	C, I	C, I ²	C, I	–	–	–	–
CS196	–	–	–	C, I	C, I	C, I	–	–
FG144	–	–	–	C, I	C, I	C, I	C, I	C, I
FG256	–	–	–	–	–	C, I	C, I	C, I
CS281	–	–	–	–	–	–	C, I	C, I
FG484	–	–	–	–	–	C, I	C, I	C, I

Notes:

1. AGL015 is not recommended for new designs.

2. Package not available.

C = Commercial temperature range: 0°C to 85°C junction temperature.

I = Industrial temperature range: –40°C to 100°C junction temperature.

IGLOO Device Status

IGLOO Devices	Status	M1 IGLOO Devices	Status
AGL015	Not recommended for new designs.		
AGL030	Production		
AGL060	Production		
AGL125	Production		
AGL250	Production	M1AGL250	Production
AGL400	Production		
AGL600	Production	M1AGL600	Production
AGL1000	Production	M1AGL1000	Production

References made to IGLOO devices also apply to ARM-enabled IGLOOe devices. The ARM-enabled part numbers start with M1 (Cortex-M1).

Contact your local Microsemi SoC Products Group representative for device availability:
www.microsemi.com/soc/contact/default.aspx.

AGL015 and AGL030

The AGL015 and AGL030 are architecturally compatible; there are no RAM or PLL features.

Devices Not Recommended For New Designs

AGL015 is not recommended for new designs.

field upgrades with confidence that valuable intellectual property cannot be compromised or copied. Secure ISP can be performed using the industry-standard AES algorithm. The IGLOO family device architecture mitigates the need for ASIC migration at higher user volumes. This makes the IGLOO family a cost-effective ASIC replacement solution, especially for applications in the consumer, networking/communications, computing, and avionics markets.

Firm-Error Immunity

Firm errors occur most commonly when high-energy neutrons, generated in the upper atmosphere, strike a configuration cell of an SRAM FPGA. The energy of the collision can change the state of the configuration cell and thus change the logic, routing, or I/O behavior in an unpredictable way. These errors are impossible to prevent in SRAM FPGAs. The consequence of this type of error can be a complete system failure. Firm errors do not exist in the configuration memory of IGLOO flash-based FPGAs. Once it is programmed, the flash cell configuration element of IGLOO FPGAs cannot be altered by high-energy neutrons and is therefore immune to them. Recoverable (or soft) errors occur in the user data SRAM of all FPGA devices. These can easily be mitigated by using error detection and correction (EDAC) circuitry built into the FPGA fabric.

Advanced Flash Technology

The IGLOO family offers many benefits, including nonvolatility and reprogrammability, through an advanced flash-based, 130-nm LVCMOS process with seven layers of metal. Standard CMOS design techniques are used to implement logic and control functions. The combination of fine granularity, enhanced flexible routing resources, and abundant flash switches allows for very high logic utilization without compromising device routability or performance. Logic functions within the device are interconnected through a four-level routing hierarchy.

IGLOO family FPGAs utilize design and process techniques to minimize power consumption in all modes of operation.

Advanced Architecture

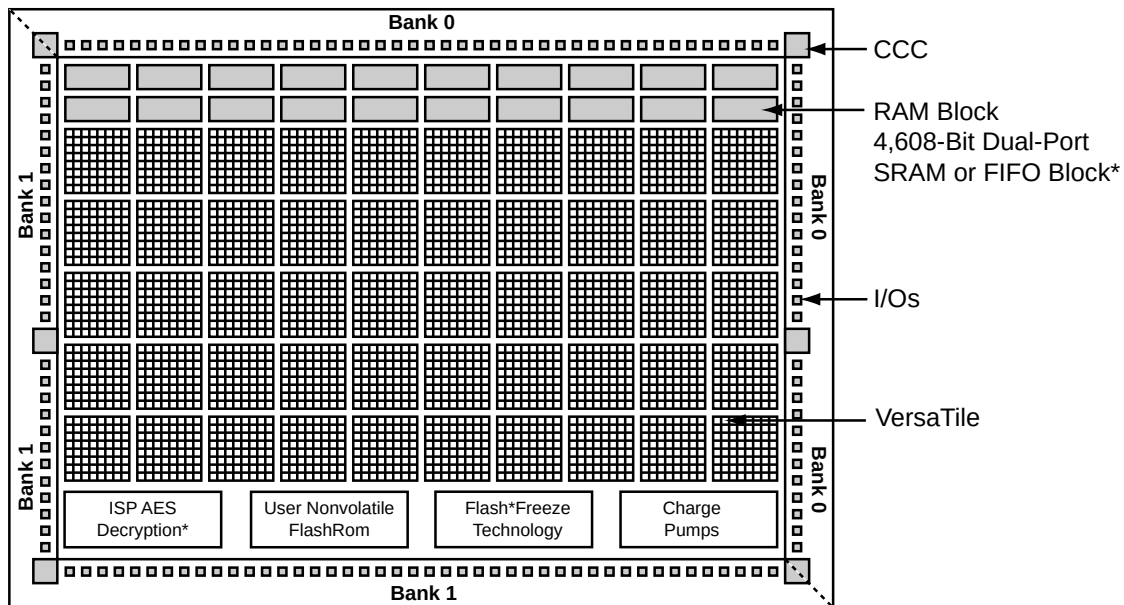
The proprietary IGLOO architecture provides granularity comparable to standard-cell ASICs. The IGLOO device consists of five distinct and programmable architectural features (Figure 1-1 on page 1-4 and Figure 1-2 on page 1-4):

- Flash*Freeze technology
- FPGA VersaTiles
- Dedicated FlashROM
- Dedicated SRAM/FIFO memory[†]
- Extensive CCCs and PLLs[†]
- Advanced I/O structure

The FPGA core consists of a sea of VersaTiles. Each VersaTile can be configured as a three-input logic function, a D-flip-flop (with or without enable), or a latch by programming the appropriate flash switch interconnections. The versatility of the IGLOO core tile as either a three-input lookup table (LUT) equivalent or a D-flip-flop/latch with enable allows for efficient use of the FPGA fabric. The VersaTile capability is unique to the ProASIC[®] family of third-generation-architecture flash FPGAs.

[†] The AGL015 and AGL030 do not support PLL or SRAM.

VersaTiles are connected with any of the four levels of routing hierarchy. Flash switches are distributed throughout the device to provide nonvolatile, reconfigurable interconnect programming. Maximum core utilization is possible for virtually any design.



Note: *Not supported by AGL015 and AGL030 devices

Figure 1-1 • IGLOO Device Architecture Overview with Two I/O Banks (AGL015, AGL030, AGL060, and AGL125)

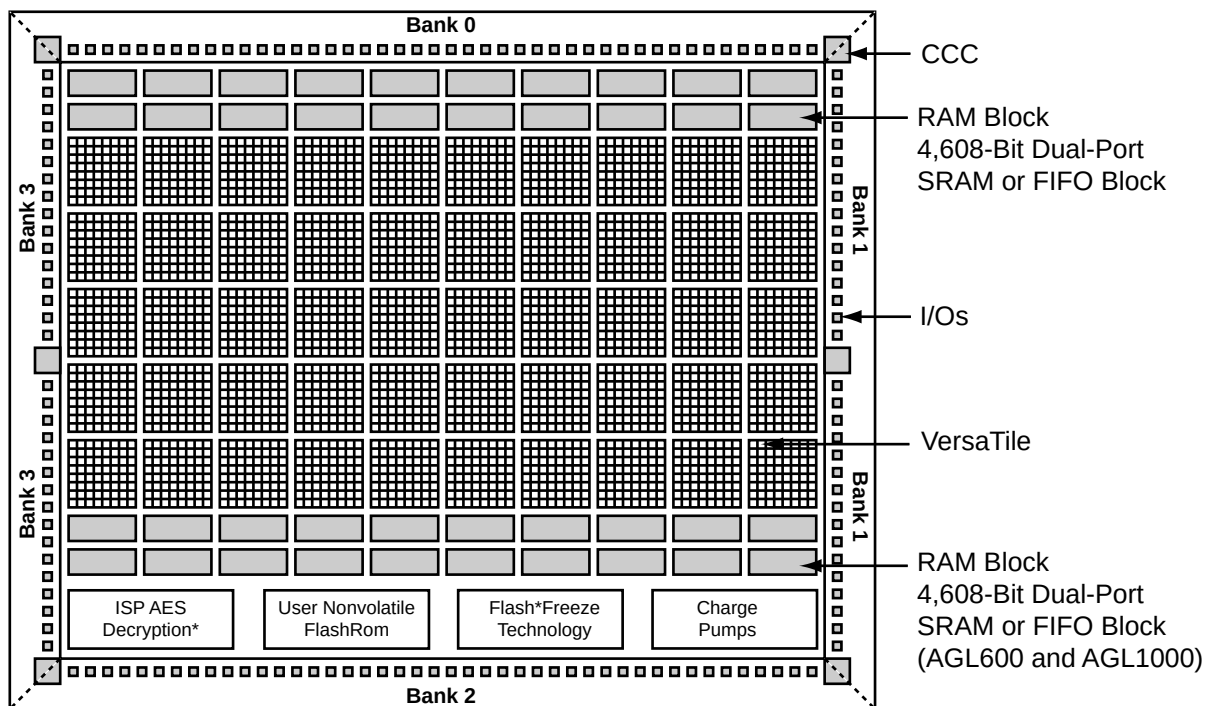


Figure 1-2 • IGLOO Device Architecture Overview with Four I/O Banks (AGL250, AGL600, AGL400, and AGL1000)

Power Calculation Methodology

This section describes a simplified method to estimate power consumption of an application. For more accurate and detailed power estimations, use the SmartPower tool in Microsemi Libero SoC software.

The power calculation methodology described below uses the following variables:

- The number of PLLs as well as the number and the frequency of each output clock generated
- The number of combinatorial and sequential cells used in the design
- The internal clock frequencies
- The number and the standard of I/O pins used in the design
- The number of RAM blocks used in the design
- Toggle rates of I/O pins as well as VersaTiles—guidelines are provided in Table 2-23 on page 2-19.
- Enable rates of output buffers—guidelines are provided for typical applications in Table 2-24 on page 2-19.
- Read rate and write rate to the memory—guidelines are provided for typical applications in Table 2-24 on page 2-19. The calculation should be repeated for each clock domain defined in the design.

Methodology

Total Power Consumption— P_{TOTAL}

$$P_{TOTAL} = P_{STAT} + P_{DYN}$$

P_{STAT} is the total static power consumption.

P_{DYN} is the total dynamic power consumption.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = (P_{DC1} \text{ or } P_{DC2} \text{ or } P_{DC3}) + N_{BANKS} * P_{DC5} + N_{INPUTS} * P_{DC6} + N_{OUTPUTS} * P_{DC7}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

N_{BANKS} is the number of I/O banks powered in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (P_{AC1} + N_{SPINE} * P_{AC2} + N_{ROW} * P_{AC3} + N_{S-CELL} * P_{AC4}) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the "Spine Architecture" section of the *IGLOO FPGA Fabric User Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

P_{AC1} , P_{AC2} , P_{AC3} , and P_{AC4} are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (P_{AC5} + \alpha_1 / 2 * P_{AC6}) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in Table 2-23 on page 2-19.

F_{CLK} is the global clock signal frequency.

Table 2-39 • I/O Output Buffer Maximum Resistances¹
Applicable to Standard Plus I/O Banks

Standard	Drive Strength	$R_{PULL-DOWN}$ (Ω) ²	$R_{PULL-UP}$ (Ω) ³
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
1.2 V LVCMOS ⁴	2 mA	158	164
1.2 V LVCMOS Wide Range ⁴	100 μ A	Same as regular 1.2 V LVCMOS	Same as regular 1.2 V LVCMOS
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2. $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / I_{OL_{spec}}$
3. $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / I_{OH_{spec}}$
4. Applicable to IGLOO V2 Devices operating at $VCCI \geq VCC$

Table 2-42 • I/O Short Currents IOSH/IOSL
Applicable to Advanced I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	132	127
	24 mA	268	181
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
	16 mA	83	87
	24 mA	169	124
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	45	51
	12 mA	91	74
	16 mA	91	74
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
	6 mA	32	39
	8 mA	66	55
	12 mA	66	55
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 μ A	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: * $T_J = 100^{\circ}\text{C}$

Table 2-43 • I/O Short Currents IOSH/IOSL
Applicable to Standard Plus I/O Banks

	Drive Strength	IOSL (mA)*	IOSH (mA)*
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	25	27
	4 mA	25	27
	6 mA	51	54
	8 mA	51	54
	12 mA	103	109
	16 mA	103	109
3.3 V LVCMOS Wide Range	100 μ A	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	16	18
	4 mA	16	18
	6 mA	32	37
	8 mA	32	37
	12 mA	65	74
1.8 V LVCMOS	2 mA	9	11
	4 mA	17	22
	6 mA	35	44
	8 mA	35	44
1.5 V LVCMOS	2 mA	13	16
	4 mA	25	33
1.2 V LVCMOS	2 mA	20	26
1.2 V LVCMOS Wide Range	100 μ A	20	26
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	103	109

Note: * $T_J = 100^\circ\text{C}$

Table 2-60 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Plus Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
4 mA	Std.	1.55	2.89	0.26	0.97	1.10	2.93	2.38	2.53	2.96	8.72	8.17	ns
6 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
8 mA	Std.	1.55	2.50	0.26	0.97	1.10	2.54	2.04	2.77	3.37	8.33	7.82	ns
12 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns
16 mA	Std.	1.55	2.31	0.26	0.97	1.10	2.34	1.86	2.93	3.64	8.12	7.65	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-61 • 3.3 V LVTTL / 3.3 V LVCMOS Low Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
4 mA	Std.	1.55	4.39	0.26	0.94	1.10	4.46	3.91	2.17	2.44	ns
6 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns
8 mA	Std.	1.55	3.72	0.26	0.94	1.10	3.78	3.43	2.40	2.85	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-62 • 3.3 V LVTTL / 3.3 V LVCMOS High Slew – Applies to 1.2 V DC Core Voltage
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.14 V, Worst-Case VCCI = 3.0 V
Applicable to Standard Banks

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
4 mA	Std.	1.55	2.74	0.26	0.94	1.10	2.78	2.26	2.17	2.55	ns
6 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns
8 mA	Std.	1.55	2.38	0.26	0.94	1.10	2.41	1.92	2.40	2.96	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-7 on page 2-7 for derating values.

Table 2-86 • 2.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Plus Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	Std.	0.97	2.36	0.18	1.08	0.66	2.41	2.21	1.96	1.92	6.01	5.81	ns
4 mA	Std.	0.97	2.36	0.18	1.08	0.66	2.41	2.21	1.96	1.92	6.01	5.81	ns
6 mA	Std.	0.97	1.97	0.18	1.08	0.66	2.01	1.75	2.21	2.40	5.61	5.34	ns
8 mA	Std.	0.97	1.97	0.18	1.08	0.66	2.01	1.75	2.21	2.40	5.61	5.34	ns
12 mA	Std.	0.97	1.75	0.18	1.08	0.66	1.79	1.52	2.38	2.70	5.39	5.11	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-87 • 2.5 V LVC MOS Low Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	4.27	0.18	1.04	0.66	4.36	4.06	1.71	1.62	ns
4 mA	Std.	0.97	4.27	0.18	1.04	0.66	4.36	4.06	1.71	1.62	ns
6 mA	Std.	0.97	3.54	0.18	1.04	0.66	3.61	3.48	1.95	2.08	ns
8 mA	Std.	0.97	3.54	0.18	1.04	0.66	3.61	3.48	1.95	2.08	ns

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-88 • 2.5 V LVC MOS High Slew – Applies to 1.5 V DC Core Voltage**Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V****Applicable to Standard Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	Units
2 mA	Std.	0.97	2.24	0.18	1.04	0.66	2.29	2.09	1.71	1.68	ns
4 mA	Std.	0.97	2.24	0.18	1.04	0.66	2.29	2.09	1.71	1.68	ns
6 mA	Std.	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns
8 mA	Std.	0.97	1.88	0.18	1.04	0.66	1.92	1.63	1.95	2.15	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

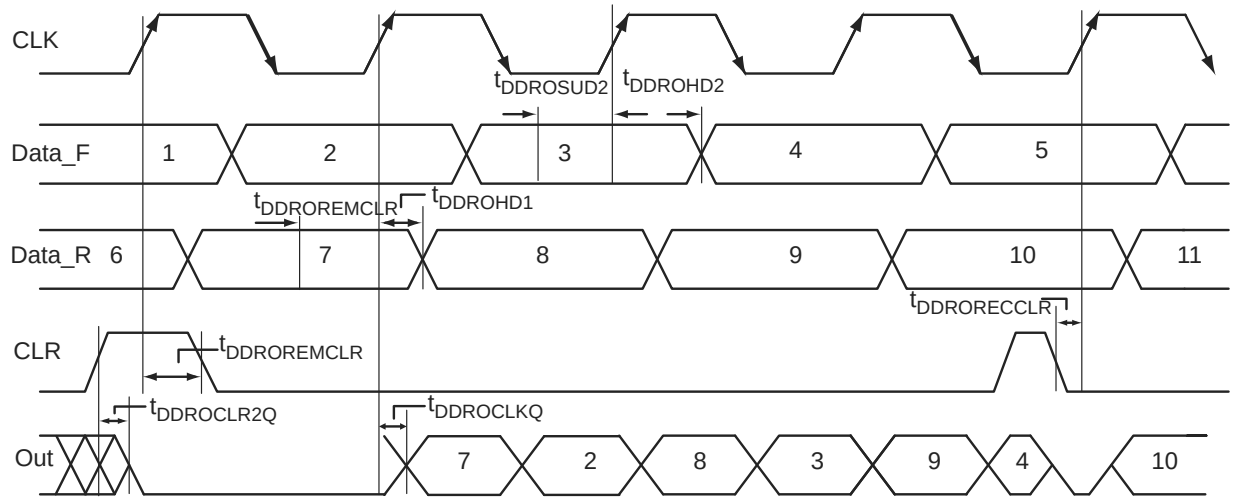


Figure 2-24 • Output DDR Timing Diagram

Timing Characteristics

1.5 V DC Core Voltage

Table 2-167 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{DDROCLKQ}	Clock-to-Out of DDR for Output DDR	1.07	ns
t_{DDROSUD1}	Data_F Data Setup for Output DDR	0.67	ns
t_{DDROSUD2}	Data_R Data Setup for Output DDR	0.67	ns
t_{DDROHD1}	Data_F Data Hold for Output DDR	0.00	ns
t_{DDROHD2}	Data_R Data Hold for Output DDR	0.00	ns
$t_{\text{DDROCLR2Q}}$	Asynchronous Clear-to-Out for Output DDR	1.38	ns
$t_{\text{DDROEMCLR}}$	Asynchronous Clear Removal Time for Output DDR	0.00	ns
$t_{\text{DDROECCLR}}$	Asynchronous Clear Recovery Time for Output DDR	0.23	ns
$t_{\text{DDROWCLR1}}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.19	ns
$t_{\text{DDROCKMPWH}}$	Clock Minimum Pulse Width High for the Output DDR	0.31	ns
$t_{\text{DDROCKMPWL}}$	Clock Minimum Pulse Width Low for the Output DDR	0.28	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	250.00	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-183 • AGL060 Global Resource**Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.04	2.33	ns
t_{RCKH}	Input High Delay for Global Clock	2.10	2.51	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.40		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.40	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

Table 2-184 • AGL125 Global Resource**Commercial-Case Conditions: $T_J = 70^{\circ}\text{C}$, $V_{CC} = 1.14\text{ V}$**

Parameter	Description	Std.		Units
		Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	2.08	2.54	ns
t_{RCKH}	Input High Delay for Global Clock	2.15	2.77	ns
t_{RCKMPWH}	Minimum Pulse Width High for Global Clock	1.40		ns
t_{RCKMPWL}	Minimum Pulse Width Low for Global Clock	1.65		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.62	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

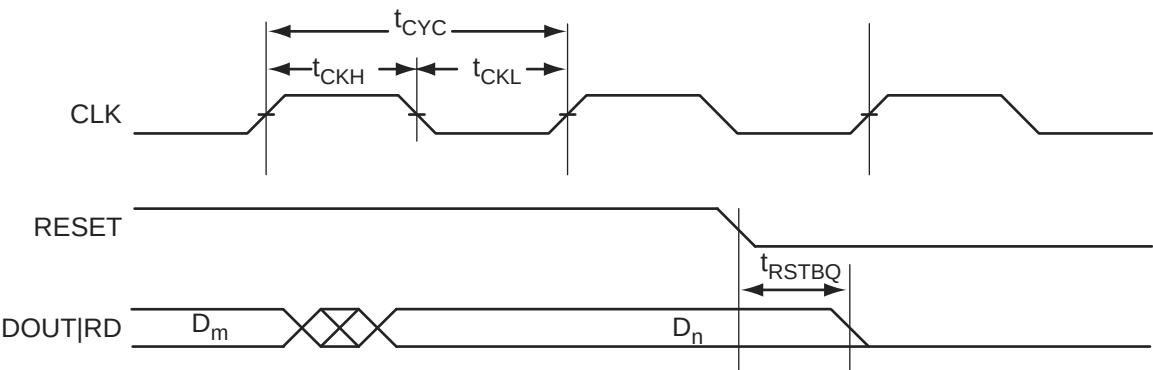


Figure 2-36 • RAM Reset. Applicable to Both RAM4K9 and RAM512x18.

Timing Characteristics

1.5 V DC Core Voltage

Table 2-191 • RAM4K9

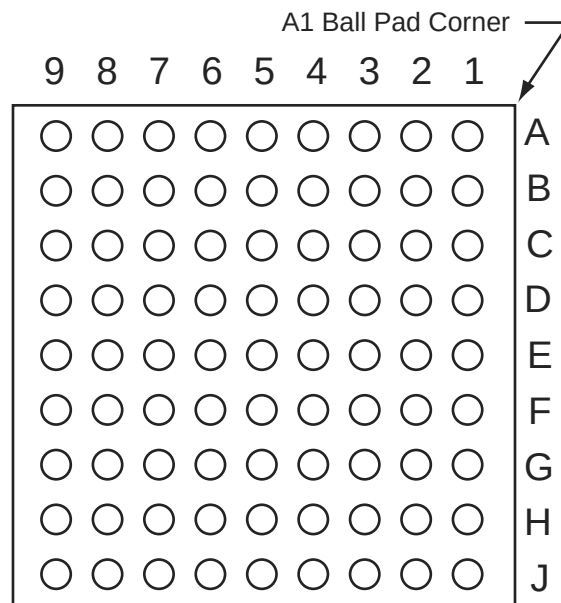
Commercial-Case Conditions: $T_J = 70^\circ\text{C}$, Worst-Case $V_{CC} = 1.425\text{ V}$

Parameter	Description	Std.	Units
t_{AS}	Address setup time	0.83	ns
t_{AH}	Address hold time	0.16	ns
t_{ENS}	REN, WEN setup time	0.81	ns
t_{ENH}	REN, WEN hold time	0.16	ns
t_{BKS}	BLK setup time	1.65	ns
t_{BKH}	BLK hold time	0.16	ns
t_{DS}	Input data (DIN) setup time	0.71	ns
t_{DH}	Input data (DIN) hold time	0.36	ns
t_{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	3.53	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	3.06	ns
t_{CKQ2}	Clock High to new data valid on DOUT (pipelined)	1.81	ns
t_{C2CWWL}^1	Address collision clk-to-clk delay for reliable write after write on same address – Applicable to Closing Edge	0.23	ns
t_{C2CRWL}^1	Address collision clk-to-clk delay for reliable read access after write on same address – Applicable to Opening Edge	0.35	ns
t_{C2CWRH}^1	Address collision clk-to-clk delay for reliable write access after read on same address – Applicable to Opening Edge	0.41	ns
t_{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	2.06	ns
	RESET Low to data out Low on DOUT (pipelined)	2.06	ns
$t_{REMRSTB}$	RESET removal	0.61	ns
$t_{RECRSTB}$	RESET recovery	3.21	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.68	ns
t_{CYC}	Clock cycle time	6.24	ns
F_{MAX}	Maximum frequency	160	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.
2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-7 for derating values.

CS81



Note: This is the bottom view of the package.

Note

For more information on package drawings, see *PD3068: Package Mechanical Drawings*.

CS196	
Pin Number	AGL400 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAC0/IO04RSB0
A4	GAC1/IO05RSB0
A5	IO14RSB0
A6	IO18RSB0
A7	IO26RSB0
A8	IO29RSB0
A9	IO36RSB0
A10	GBC0/IO54RSB0
A11	GBB0/IO56RSB0
A12	GBB1/IO57RSB0
A13	GBA1/IO59RSB0
A14	GND
B1	VCCIB3
B2	VMV0
B2	VMV0
B3	GAA1/IO01RSB0
B4	GAB1/IO03RSB0
B5	GND
B6	IO17RSB0
B7	IO25RSB0
B8	IO34RSB0
B9	IO39RSB0
B10	GND
B11	GBC1/IO55RSB0
B12	GBA0/IO58RSB0
B13	GBA2/IO60PPB1
B14	GBB2/IO61PDB1
C1	GAC2/IO153UDB3
C2	GAB2/IO154UDB3
C3	GNDQ
C4	VCCIB0
C5	GAB0/IO02RSB0
C6	IO15RSB0
C7	VCCIB0

CS196	
Pin Number	AGL400 Function
C8	IO31RSB0
C9	IO44RSB0
C10	IO49RSB0
C11	VCCIB0
C12	IO60NPB1
C13	GNDQ
C14	IO61NDB1
D1	IO153VDB3
D2	IO154VDB3
D3	GAA2/IO155UDB3
D4	IO150PPB3
D5	IO11RSB0
D6	IO20RSB0
D7	IO23RSB0
D8	IO28RSB0
D9	IO41RSB0
D10	IO47RSB0
D11	IO63PPB1
D12	VMV1
D13	IO62NDB1
D14	GBC2/IO62PDB1
E1	IO149PDB3
E2	GND
E3	IO155VDB3
E4	VCCIB3
E5	IO151USB3
E6	IO09RSB0
E7	IO12RSB0
E8	IO32RSB0
E9	IO46RSB0
E10	IO51RSB0
E11	VCCIB1
E12	IO63NPB1
E13	GND
E14	IO64PDB1
F1	IO149NDB3

CS196	
Pin Number	AGL400 Function
F2	IO144NPB3
F3	IO148PDB3
F4	IO148NDB3
F5	IO150NPB3
F6	IO07RSB0
F7	VCC
F8	VCC
F9	IO43RSB0
F10	IO73PDB1
F11	IO73NDB1
F12	IO66NDB1
F13	IO66PDB1
F14	IO64NDB1
G1	GFB1/IO146PDB3
G2	GFA0/IO145NDB3
G3	GFA2/IO144PPB3
G4	VCOMPLF
G5	GFC0/IO147NDB3
G6	VCC
G7	GND
G8	GND
G9	VCC
G10	GCC0/IO67NDB1
G11	GCB1/IO68PDB1
G12	GCA0/IO69NDB1
G13	IO72NDB1
G14	GCC2/IO72PDB1
H1	GFB0/IO146NDB3
H2	GFA1/IO145PDB3
H3	VCCPLF
H4	GFB2/IO143PPB3
H5	GFC1/IO147PDB3
H6	VCC
H7	GND
H8	GND
H9	VCC

QN132	
Pin Number	AGL125 Function
C17	IO83RSB1
C18	VCCIB1
C19	TCK
C20	VMV1
C21	VPUMP
C22	VJTAG
C23	VCCIB0
C24	NC
C25	NC
C26	GCA1/IO55RSB0
C27	GCC0/IO52RSB0
C28	VCCIB0
C29	IO42RSB0
C30	GNDQ
C31	GBA1/IO40RSB0
C32	GBB0/IO37RSB0
C33	VCC
C34	IO24RSB0
C35	IO19RSB0
C36	IO16RSB0
C37	IO10RSB0
C38	VCCIB0
C39	GAB1/IO03RSB0
C40	VMV0
D1	GND
D2	GND
D3	GND
D4	GND

FG144		FG144		FG144	
Pin Number	AGL400 Function	Pin Number	AGL400 Function	Pin Number	AGL400 Function
A1	GNDQ	D1	IO149NDB3	G1	GFA1/IO145PPB3
A2	VMV0	D2	IO149PDB3	G2	GND
A3	GAB0/IO02RSB0	D3	IO153VDB3	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO155UPB3	G4	GFA0/IO145NPB3
A5	IO16RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO30RSB0	D7	GBC0/IO54RSB0	G7	GND
A8	VCC	D8	GBC1/IO55RSB0	G8	GDC1/IO77UPB1
A9	IO34RSB0	D9	GBB2/IO61PDB1	G9	IO72NDB1
A10	GBA0/IO58RSB0	D10	IO61NDB1	G10	GCC2/IO72PDB1
A11	GBA1/IO59RSB0	D11	IO62NPB1	G11	IO71NDB1
A12	GNDQ	D12	GCB1/IO68PPB1	G12	GCB2/IO71PDB1
B1	GAB2/IO154UDB3	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO147NDB3	H2	GFB2/IO143PDB3
B3	GAA0/IO00RSB0	E3	GFC1/IO147PDB3	H3	GFC2/IO142PSB3
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO137PDB3
B5	IO14RSB0	E5	IO155VPB3	H5	VCC
B6	IO19RSB0	E6	VCCIB0	H6	IO75PDB1
B7	IO23RSB0	E7	VCCIB0	H7	IO75NDB1
B8	IO31RSB0	E8	GCC1/IO67PDB1	H8	GDB2/IO81RSB2
B9	GBB0/IO56RSB0	E9	VCCIB1	H9	GDC0/IO77VPB1
B10	GBB1/IO57RSB0	E10	VCC	H10	VCCIB1
B11	GND	E11	GCA0/IO69NDB1	H11	IO73PSB1
B12	VMV1	E12	IO70NDB1	H12	VCC
C1	IO154VDB3	F1	GFB0/IO146NPB3	J1	GEB1/IO136PDB3
C2	GFA2/IO144PPB3	F2	VCOMPLF	J2	IO143NDB3
C3	GAC2/IO153UDB3	F3	GFB1/IO146PPB3	J3	VCCIB3
C4	VCC	F4	IO144NPB3	J4	GEC0/IO137NDB3
C5	IO12RSB0	F5	GND	J5	IO125RSB2
C6	IO17RSB0	F6	GND	J6	IO116RSB2
C7	IO25RSB0	F7	GND	J7	VCC
C8	IO32RSB0	F8	GCC0/IO67NDB1	J8	TCK
C9	IO53RSB0	F9	GCB0/IO68NPB1	J9	GDA2/IO80RSB2
C10	GBA2/IO60PDB1	F10	GND	J10	TDO
C11	IO60NDB1	F11	GCA1/IO69PDB1	J11	GDA1/IO79UDB1
C12	GBC2/IO62PPB1	F12	GCA2/IO70PDB1	J12	GDB1/IO78UDB1

FG484	
Pin Number	AGL600 Function
A1	GND
A2	GND
A3	VCCIB0
A4	NC
A5	NC
A6	IO09RSB0
A7	IO15RSB0
A8	NC
A9	NC
A10	IO22RSB0
A11	IO23RSB0
A12	IO29RSB0
A13	IO35RSB0
A14	NC
A15	NC
A16	IO46RSB0
A17	IO48RSB0
A18	NC
A19	NC
A20	VCCIB0
A21	GND
A22	GND
AA1	GND
AA2	VCCIB3
AA3	NC
AA4	NC
AA5	NC
AA6	IO135RSB2
AA7	IO133RSB2
AA8	NC
AA9	NC
AA10	NC
AA11	NC
AA12	NC
AA13	NC
AA14	NC

FG484	
Pin Number	AGL600 Function
AA15	NC
AA16	IO101RSB2
AA17	NC
AA18	NC
AA19	NC
AA20	NC
AA21	VCCIB1
AA22	GND
AB1	GND
AB2	GND
AB3	VCCIB2
AB4	NC
AB5	NC
AB6	IO130RSB2
AB7	IO128RSB2
AB8	IO122RSB2
AB9	IO116RSB2
AB10	NC
AB11	NC
AB12	IO113RSB2
AB13	IO112RSB2
AB14	NC
AB15	NC
AB16	IO100RSB2
AB17	IO95RSB2
AB18	NC
AB19	NC
AB20	VCCIB2
AB21	GND
AB22	GND
B1	GND
B2	VCCIB3
B3	NC
B4	NC
B5	NC
B6	IO08RSB0

FG484	
Pin Number	AGL600 Function
B7	IO12RSB0
B8	NC
B9	NC
B10	IO17RSB0
B11	NC
B12	NC
B13	IO36RSB0
B14	NC
B15	NC
B16	IO47RSB0
B17	IO49RSB0
B18	NC
B19	NC
B20	NC
B21	VCCIB1
B22	GND
C1	VCCIB3
C2	NC
C3	NC
C4	NC
C5	GND
C6	NC
C7	NC
C8	VCC
C9	VCC
C10	NC
C11	NC
C12	NC
C13	NC
C14	VCC
C15	VCC
C16	NC
C17	NC
C18	GND
C19	NC
C20	NC

FG484	
Pin Number	AGL1000 Function
H19	IO87PDB1
H20	VCC
H21	NC
H22	NC
J1	IO212NDB3
J2	IO212PDB3
J3	NC
J4	IO217NDB3
J5	IO218NDB3
J6	IO216PDB3
J7	IO216NDB3
J8	VCCIB3
J9	GND
J10	VCC
J11	VCC
J12	VCC
J13	VCC
J14	GND
J15	VCCIB1
J16	IO83NPB1
J17	IO86NPB1
J18	IO90PPB1
J19	IO87NDB1
J20	NC
J21	IO89PDB1
J22	IO89NDB1
K1	IO211PDB3
K2	IO211NDB3
K3	NC
K4	IO210PPB3
K5	IO213NDB3
K6	IO213PDB3
K7	GFC1/IO209PPB3
K8	VCCIB3
K9	VCC
K10	GND

FG484	
Pin Number	AGL1000 Function
U1	IO195PDB3
U2	IO195NDB3
U3	IO194NPB3
U4	GEB1/IO189PDB3
U5	GEB0/IO189NDB3
U6	VMV2
U7	IO179RSB2
U8	IO171RSB2
U9	IO165RSB2
U10	IO159RSB2
U11	IO151RSB2
U12	IO137RSB2
U13	IO134RSB2
U14	IO128RSB2
U15	VMV1
U16	TCK
U17	VPUMP
U18	TRST
U19	GDA0/IO113NDB1
U20	NC
U21	IO108NDB1
U22	IO109PDB1
V1	NC
V2	NC
V3	GND
V4	GEA1/IO188PDB3
V5	GEA0/IO188NDB3
V6	IO184RSB2
V7	GEC2/IO185RSB2
V8	IO168RSB2
V9	IO163RSB2
V10	IO157RSB2
V11	IO149RSB2
V12	IO143RSB2
V13	IO138RSB2
V14	IO131RSB2